Tight binding in diamond anc zinc-blende crystals

- Tight binding approximation for tetrahedrally coordinated orbitals
- •Combination of s, p_x , p_y and p_z orbitals: the sp³ model
- Orbital symmetry and overlap integrals
- •The sp³s* model
- The bandstructure of Si, Ge and GaAs

Hamiltonian

$$H_c|\Psi_{\mathbf{k}}>=E(\mathbf{k})|\Psi_{\mathbf{k}}>,$$

The guess wavefunction: summation of wavefunctions placed on the atomic sites

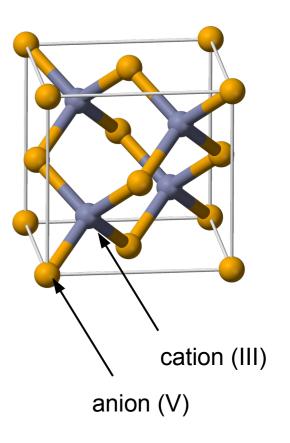
$$\Psi_{\mathbf{k}} = \sum_{\mathbf{R}} \exp(i\mathbf{R}\mathbf{k}) \left(\phi_a(\mathbf{r} - \mathbf{R}) + \exp(i\mathbf{d}\mathbf{k}) \phi_c(\mathbf{r} - \mathbf{R} - \mathbf{d})\right),$$

Each wavefunction is the linear combination of different orbitals

$$\phi_a(\mathbf{r}) = a_s \phi_a^s(\mathbf{r}) + a_{p_x} \phi_a^{p_x}(\mathbf{r}) + a_{p_y} \phi_a^{p_y}(\mathbf{r}) + a_{p_z} \phi_a^{p_z}(\mathbf{r})$$
$$= \sum_{i=s, p_x, p_y, p_z} a_i \phi_a^i(\mathbf{r}),$$

$$\phi_c(\mathbf{r} - \mathbf{d}) = c_s \phi_c^s(\mathbf{r} - \mathbf{d}) + c_{p_x} \phi_c^{p_x}(\mathbf{r} - \mathbf{d}) + c_{p_y} \phi_c^{p_y}(\mathbf{r} - \mathbf{d}) + c_{p_z} \phi_c^{p_z}(\mathbf{r} - \mathbf{d})$$

$$= \sum_{i=s, p_x, p_y, p_z} c_i \phi_c^i(r),$$

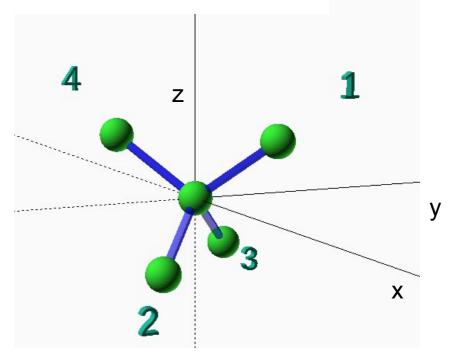


If we limit the interaction over near-neighbours the summation is limited to the four tetrahedrally coordinated atoms around a central atom

$$\Psi_{\mathbf{k}} = \phi_a(\mathbf{r}) + \sum_{\mathbf{d}} \exp(i\mathbf{d}\mathbf{k}) \,\phi_c(\mathbf{r} - \mathbf{d}),$$

$$= \sum_{n=s, p_x, p_y, p_z} a_n \phi_a^n(r) + \sum_{\mathbf{d}} \exp(i\mathbf{d}\mathbf{k}) \sum_{n=s, p_x, p_y, p_z} c_n \phi_c^n(r - \mathbf{d})$$

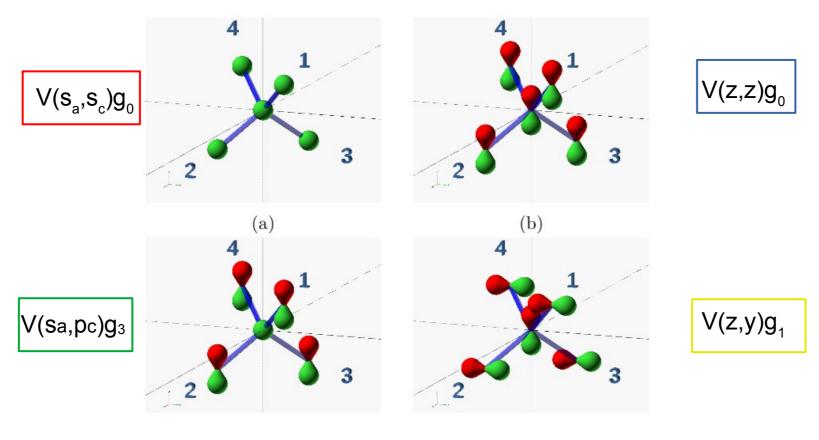
$$\begin{aligned} \mathbf{d_1} &= \frac{a}{4}[1, 1, 1] \\ \mathbf{d_2} &= \frac{a}{4}[1, -1, -1] \\ \mathbf{d_3} &= \frac{a}{4}[-1, 1, -1] \\ \mathbf{d_4} &= \frac{a}{4}[-1, -1, 1]. \end{aligned}$$



	ϕ_a^s	ϕ_c^s	$\phi_a^{p_x}$	$\phi_c^{p_x}$	$\phi_a^{p_y}$	$\phi_c^{p_y}$	$\phi_a^{p_z}$	$\phi_c^{p_z}$
ϕ_a^s	E(s,a)	$V(s_a, s_c)g_0$	0	$V(s_a, p_c)g_1$	0	$V(s_a, p_c)g_2$	0	$V(s_a, p_c)g_3$
ϕ_c^s	$V(s_a, s_c)g_0^*$	E(s,c)	$-V(s_c, p_a)g_1^*$	0	$-V(s_c, p_a)g_2^*$	0	$-V(s_c, p_a)g_3^*$	0
$\phi_a^{p_x}$	0	$-V(s_c, p_a)g_1$	E(p,a)	$V(z,z)g_0$	0	$V(z,y)g_3$	0	$V(z,y)g_2$
$\phi_c^{p_x}$	$V(s_a, p_c)g_1^*$	0	$V(z,z)g_0^*$	E(p,c)	$V(z,y)g_3^*$	0	$V(z,y)g_2^{\ast}$	0
$\phi_a^{p_y}$	0	$-V(s_c, p_a)g_2$	0	$V(z,y)g_3$	E(p,a)	$V(z,z)g_0$	0	$V(z,y)g_1$
$\phi_c^{p_y}$	$V(s_a, p_c)g_2^*$	0	$V(z,y)g_3^*$	0	$V(z,z)g_0^*$	E(p,c)	$V(z,y)g_1^{\ast}$	0
$\phi_a^{p_z}$	0	$-V(s_c, p_a)g_3$	0	$V(z,y)g_2$	0	$V(z,y)g_1$	E(p,a)	$V(z,z)g_0$
$\phi_c^{p_z}$	$V(s_a, p_c)g_3^*$	0	$V(z,y)g_2^{\ast}$	0	$V(z,y)g_1^{\ast}$	0	$V(z,z)g_0^*$	E(p,c)

Diagonal terms are obtained by the overlap of the same atomic orbital on the same atomic site

Null term are obtain by the overlap of orbitals of different parity on the same atomic site



$$g_0(\mathbf{k}) = \frac{1}{4} \left(+ \exp\left(i\mathbf{k}\,\mathbf{d_1}\right) + \exp\left(i\mathbf{k}\,\mathbf{d_2}\right) + \exp\left(i\mathbf{k}\,\mathbf{d_3}\right) + \exp\left(i\mathbf{k}\,\mathbf{d_4}\right) \right)$$

$$g_1(\mathbf{k}) = \frac{1}{4} \left(+ \exp\left(i\mathbf{k}\,\mathbf{d_1}\right) + \exp\left(i\mathbf{k}\,\mathbf{d_2}\right) - \exp\left(i\mathbf{k}\,\mathbf{d_3}\right) - \exp\left(i\mathbf{k}\,\mathbf{d_4}\right) \right)$$

$$g_2(\mathbf{k}) = \frac{1}{4} \left(+ \exp\left(i\mathbf{k}\,\mathbf{d_1}\right) - \exp\left(i\mathbf{k}\,\mathbf{d_2}\right) + \exp\left(i\mathbf{k}\,\mathbf{d_3}\right) - \exp\left(i\mathbf{k}\,\mathbf{d_4}\right) \right)$$

$$g_3(\mathbf{k}) = \frac{1}{4} \left(+ \exp\left(i\mathbf{k}\,\mathbf{d_1}\right) - \exp\left(i\mathbf{k}\,\mathbf{d_2}\right) - \exp\left(i\mathbf{k}\,\mathbf{d_3}\right) + \exp\left(i\mathbf{k}\,\mathbf{d_4}\right) \right)$$

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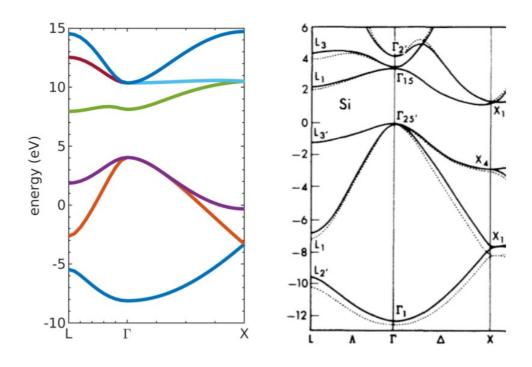
Table 3 Interaction parameters (in eV) appropriate for C, Si, and Ge when second-nearest-neighbor interactions are ignored. The parameter E_s is arbitrary

	E_s	(E_p-E_s)	V_{ss}	V_{sp}	V_{xx}	V_{xy}
)	_	7.40	-15.2	10.25	3.0	8.3
i		7.20	-8.13	5.88	3.17	7.51
łe		8.41	-6.78	5.31	2.62	6.82

Table 5

Interaction parameters (in eV) for GaAs and ZnSe. The four intra-atomic parameters E_{s_0} , E_{s_1} , E_{p_0} , and E_{p_1} give information only on the relative energy differences between the tight-binding s- and p-functions. The subscripts 0 and 1 refer to As (or Se) and Ga (or Zn), respectively

1	E_{s_0}	E_{s_1}	E_{p_0}	E_{p_1}	V_{ss}	V_{s_0p}	V_{s_1p}	V_{xx}	V_{xy}
					$-7.00 \\ -6.14$				



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Tight-Binding Calculations of the Valence Bands of Diamond and Zincblende Crystals

By

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Using the tight-binding method, the valence band structures and densities of states for C, Si, Ge, GaAs, and ZnSe are calculated. Very good agreement is obtained with other calculations when all nearest- and one second-nearest-neighbor interactions are included. The effects of the various interactions on the density of states are discussed.

A SEMI-EMPIRICAL TIGHT-BINDING THEORY OF THE ELECTRONIC STRUCTURE OF SEMICONDUCTORS†

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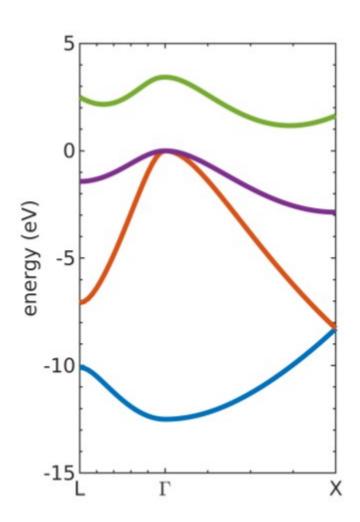
(Received 28 September 1981; accepted 19 November 1981)

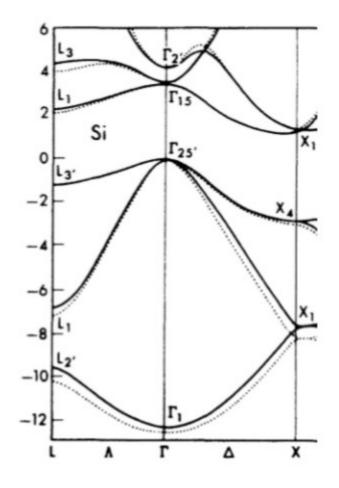
Table (A)

		sc)	(p _x a)	Pya)	pza)	p _x c)	(pyc)	(p _z c)	s*a)	s*c)
sa)	E(s,a)	V(s,s)g ₀	0	0	0	V(sa,pc)gi	V(sa,pc)g ₂	V(sa,pc)g3	0	0
BC)	V(s,s)g ₀ *	E(s,c)	-V(pa,sc)g ₁ *	-V(pa,sc)g ₂ *	-V(pa,sc)g3*	0	0	0	0	0
p _x a)	0	-V(pa,sc)g ₁	E(p,a)	0	0	V(x,x)g ₀	V(x,y)g3	V(x,y)g ₂	0	-V(pa,s*c)g1
p _v a)	0	-V(pa,sc)g ₂	0	E(p,a)	0	V(x,y)g3	V(x,x)g ₀	V(x,y)g1	0	-V(pa,s*c)g ₂
p _z a)	0	-V(pa,sc)g ₃	0	0	E(p,a)	V(x,y)g ₂	V(x,y)g ₁	V(x,x)g ₀	0	-V(pa,s*c)g3
p _x c)	V(sa,pc)g ₁ *	0	V(x,x)g0*	V(x,y)g3*	V(x,y)g2*	E(p,c)	0	0	V(s*a,pc)g1	0
p _y c)	V(sa,pc)g2*	0	V(x,y)g3*	V(x,x)g0*	V(x,y)g1*	0	E(p,c)	0	V(s*s,pc)g2	0
(pzc)	V(es,pc)g3*	0	V(x,y)g2*	V(x,y)g ₁ *	V(x,x)g ₀ *	0	0	E(p,c)	V(s*a,pc)g3	0
s*a)	0	0	0	0	0	V(s*a,pc)g1	V(s*a,pc)g2	V(a*a,pc)g3	E(s*,a)	V(s*,s*)g _O
s*c)	0	. 0	-V(pa,s*c)g ₁ *	-V(pa,s*c)g2*	-V(pa,s*c)g3*	0	0	0	V(s*,s*)g ₀ *	E(s*,c)

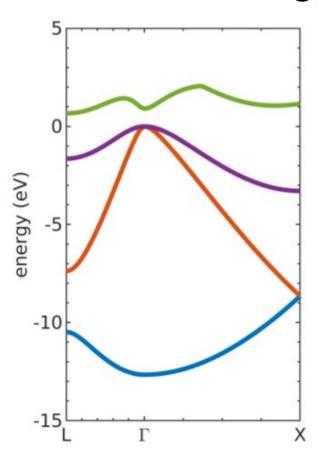
Table 1. Empirical matrix elements of the sp3s* Hamiltonian in eV. Although only three digits are significant, we reproduce the actual numbers used to generate the figures in order to eliminate any problem with round-off errors Compound E(s,a) E(p,a) E(s,c) E(p,c) E(s*,a) E(a*,c) -4.5450 3.8400 -4.5450 3.8400 11.3700 11.3700 Sí -4.2000 1.7150 -4.2000 1.7150 6.6850 6.6850 Ge -5.8800 1.6100 -5.8800 1.6100 6.3900 6.3900 Sn -5.6700 1.3300 -5.6700 1.3300 5.9000 5.9000 SIC -8.4537 2.1234 -4.8463 4.3466 9.6534 9.3166 AIP -7.8466 1.3169 -1.25344.2831 8.7069 7.4231 AlAn -7.5273 0.9833 -1.1627 3.5867 7.4833 A1Sb -6.1714 0.9807 -2.0716 3.0163 6.7607 6.1543 GaP -8.1124 1.1250 -2.1976 4.1150 8.5150 7.1850 GaAs -8.3431 1.0414 -2.6569 3,6686 8.5014 6.7500 GaSb 7.3207 0.8554 3,8993 InP -8.5274 0.8735 -1.4826 4.0465 8.2635 InAs -9.5381 0.9099 -2.7219 3.7201 7.4099 6.7401 InSb -8.01570.6738 -3.46432.9162 6.4530 5,9362 ZnSe -11.8383 1.5072 0.0183 5.9928 7.5872 8.9928 ZnTe -9.8150 -7.1256 1.4834 **→0.9350** 7.0834 Compound V(s,s) V(x,y) V(sa,pc) V(sc,pa) V(s*a,pc) V(pa,s*c) V(x,x) Visage) Visage) Visage) Viga, 50 C -22.7250 3.8400 11.6700 15.2206 15,2206 8,2109 8.2109 SI -8.3000 1.7150 4.5750 5.7292 5.7292 5.3749 5.3749 Ge -6.7800 1.6100 4.9000 5.4649 5.4640 5:2191 5-2191 4.9617 4.9617 4.5434 4.5434 -5.6700 1.3300 4.0800 4.1785 4.3138 3.9665 3.9665 4. 2288 4.6288 3.9665 3.9665 Sic -12.4197 3.0380 5.9216 914900 9.2007 8.7138 4.4051 AIP -7.4535 2.3749 4.8378 562451 5.2775 5.2508 4.6388 ALA -6.6642 1.8780 4.2919 5.1106 5.4965 4.5216 4.9950 Alsh -5.6448 1.7199 3.6648 4.9121 4.2137 4.3662 3.0739 GaP -7.4709 2.1516 5.1369 4.2771 6.3190 4.6541 5.0950 GaAs -6.4513 1.9546 5.0779 5-7039 4-0422 4-8077 4.7545 4.2547 Cost 4.2485 5.2671 1.5709 4-1285 4-9601 InP 4.2180 -5.3614 1.8801 4.2324 2.2265 5,5825 3.4623 4.4814 InAs -5.6052 1.8398 4.4693 3.0354 5.4389 3.3744 3.9097 InSb -5.5193 1.4018 3.8761 3.7880 4.5900 3.5666 3.4048 ZnSe -6.2163 3.0054 5.9942 3.4980 6.3191 2.5891 3.9533 ZnTe -6.5765 2,7951 5.4670 5.9827 5.8199 1.3196 0.0000 -5.9854 1.3546 4.443B 6.1693 4.4708 4. 1144

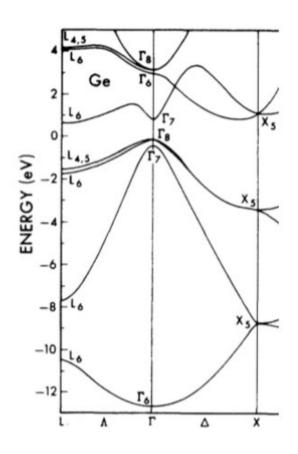
Silicon



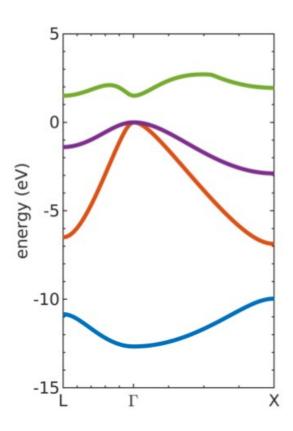


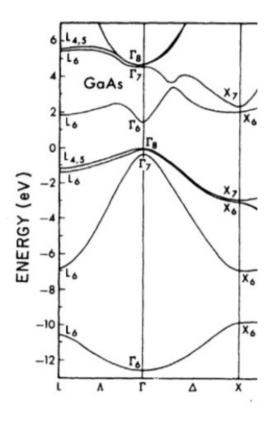
Germanium





Gallium Arsenide





Eigenvectors at k=0

$$k=0 \Gamma point$$

 $g_0 \neq 0 g_1 = g_2 = g_3 = 0$

	ϕ_a^s	ϕ_c^s	$\phi_a^{p_x}$	$\phi_c^{p_x}$	$\phi_a^{p_y}$	$\phi_c^{p_y}$	$\phi_a^{p_z}$	$\phi_c^{p_z}$
ϕ_a^s	E(s,a)	$V(s_a, s_c)g_0$	0	0	0	0	0	0
ϕ_c^s	$V(s_a, s_c)g_0^*$	E(s,c)	0	0	0	0	0	0
$\phi_a^{p_x}$	0	0	E(p,a)	$V(z,z)g_0$	0	0	0	0
$\phi_c^{p_x}$	0	0	$V(z,z)g_0^*$	E(p,c)	0	0	0	0
$\phi_a^{p_y}$	0	0	0	0	E(p,a)	$V(z,z)g_0$	0	0
$\phi_c^{p_y}$	0	0	0	0	$V(z,z)g_0^*$	E(p,c)	0	0
$\phi_a^{p_z}$	0	0	0	0	0	0	E(p,a)	$V(z,z)g_0$
$\phi_c^{p_z}$	0	0	0	0	0	0	$V(z,z)g_0^*$	E(p,c)

Table 1: 8×8 secular matrix for the sp^3 tight-binding problem at $\mathbf{k}=0$, Γ point.

2 (bonding and antibonding) s-type bands

6 (bonding and antibonding) p-type bands

Eigenvectors along k=[001]

K along [001] Δ $g_0 ≠ 0 g_3 ≠ 0 g_1 = g_2 = 0$

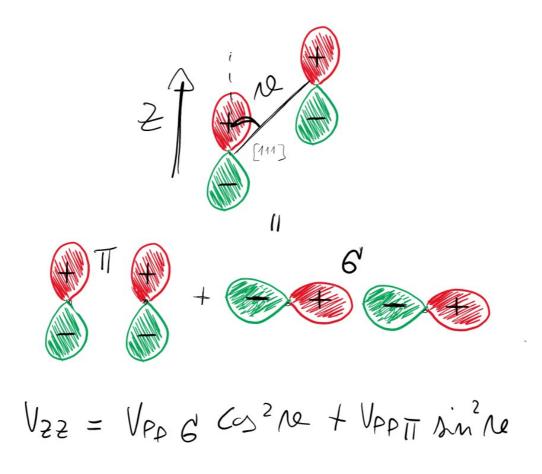
	ϕ_a^s	ϕ_c^s	$\phi_a^{p_z}$	$\phi_c^{p_z}$	$\phi_a^{p_x}$	$\phi_c^{p_x}$	$\phi_a^{p_y}$	$\phi_c^{p_y}$
ϕ_a^s	E(s,a)	$V(s_a, s_c)g_0$	0	$V(s_a, p_c)g_3$	0	0	0	0
ϕ_c^s	$V(s_a, s_c)g_0^*$	E(s,c)	$-V(s_c,p_a)g_3^*$	0	0	0	0	0
$\phi_a^{p_z}$	0	$-V(s_c, p_a)g_3$	E(p,a)	$V(z,z)g_0$	0	0	0	0
$\phi_c^{p_z}$	$V(s_a, p_c)g_3^*$	0	$V(z,z)g_0^*$	E(p,c)	0	0	0	0
$\phi_a^{p_x}$	0	0	0	0	E(p,a)	$V(z,z)g_0$	0	$V(z,y)g_3$
$\phi_c^{p_x}$	0	0	0	0	$V(z,z)g_0^*$	E(p,c)	$V(z,y)g_3^{\ast}$	
$\phi_a^{p_y}$	0	0	0	0	0	$V(z,y)g_3$	E(p,a)	$V(z,z)g_0$
$\phi_c^{p_y}$	0	0	0	0	$V(z,y)g_3^*$	0	$V(z,z)g_0^*$	E(p,c)

Table 1: 8×8 secular matrix for the sp^3 tight-binding problem along the $\mathbf{k} = [001]$ direction, Δ .

4 (bonding and antibonding) s+p_z bands

4 (bonding and antibonding) p_x and p_y bands

Valence band



Heavy and light holes

In the TB description of semiconductor bandstructure the top of the valence band (VB) originates from p-type states. Some relevant features of the VB can be understood considering a simple cubic latice of p_x , p_y , p_z orbitals.

$$m_{LH} \propto \frac{1}{V_{pp\,\sigma}}$$
 $m_{HH} \propto \frac{1}{V_{pp\,\pi}}$

In this picture we obtain two degenerate 'heavy hole' (HH) band and one "light hole" (LH) band.